

P-Channel Enhancement Mode Power MOSFET

Description

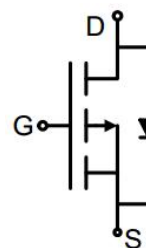
The G900P15M uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

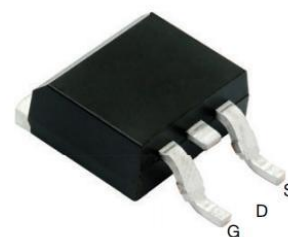
- V_{DS} -150V
- I_D (at $V_{GS} = -10V$) -35A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 80m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-263

Ordering Information

Device	Package	Marking	Packaging
G900P15M	TO-263	G900P15	800pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-150	V
Continuous Drain Current	I_D	-35	A
Pulsed Drain Current (note1)	I_{DM}	-140	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	198	W
Single pulse avalanche energy (note2)	E_{AS}	132	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	0.63	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-150	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -150V, V _{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-2.6	-4.0	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -5A	--	62	80	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -5V, I _D = -5A	--	8	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -75V, f = 1.0MHz	--	4056	--	pF
Output Capacitance	C _{oss}		--	148	--	
Reverse Transfer Capacitance	C _{rss}		--	109	--	
Total Gate Charge	Q _g	V _{DD} = -75V, I _D = -5A, V _{GS} = -10V	--	27	--	nC
Gate-Source Charge	Q _{gs}		--	7	--	
Gate-Drain Charge	Q _{gd}		--	3	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = -75V, I _D = -5A, R _G = 3Ω	--	10	--	ns
Turn-on Rise Time	t _r		--	9	--	
Turn-off Delay Time	t _{d(off)}		--	29	--	
Turn-off Fall Time	t _f		--	4	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	-35	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = -5A, V _{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = -5A, V _{GS} = 0V di/dt=-500A/us	--	434	--	nC
Reverse Recovery Time	T _{rr}		--	51	--	ns

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_J = 25^{\circ}\text{C}$, $V_{DD} = -50V$, $V_{GS} = -10V$, $L = 0.5mH$, $R_G = 25\Omega$
3. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

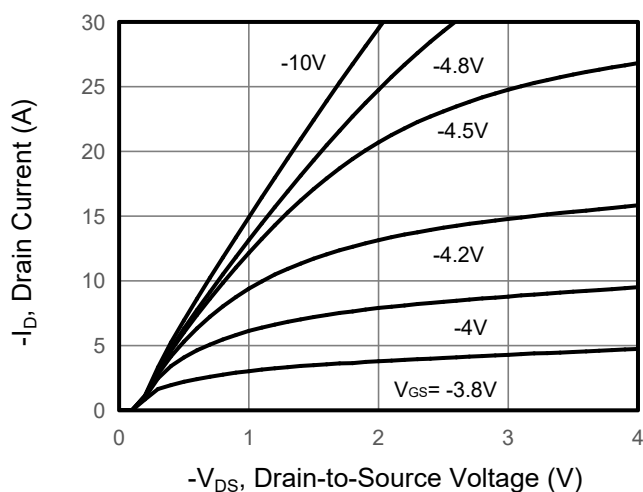


Figure 2. Transfer Characteristics

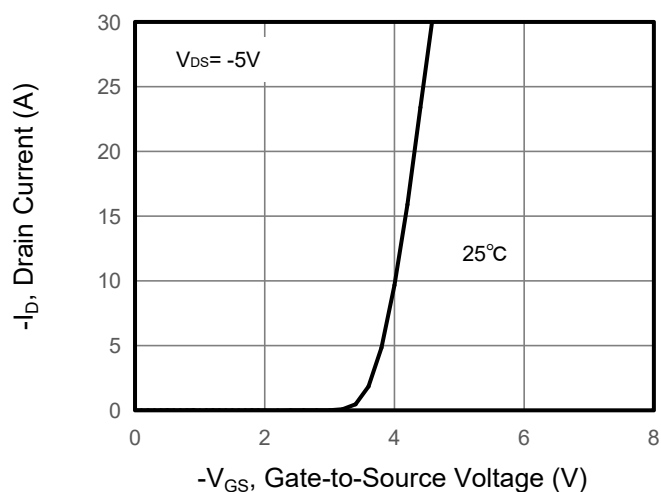


Figure 3. Drain Source On Resistance

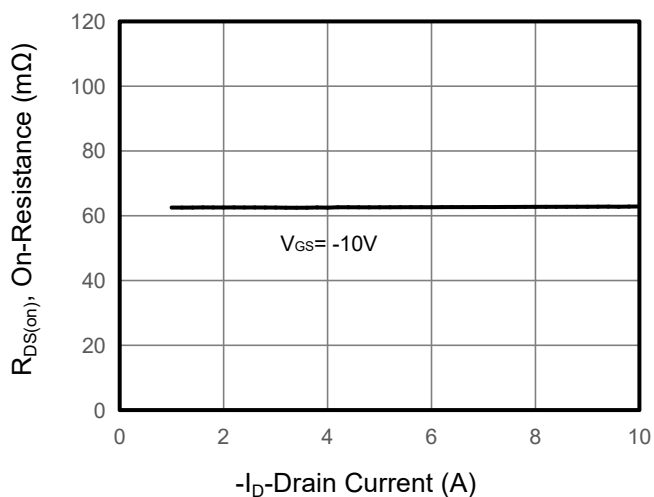


Figure 4. Gate Charge

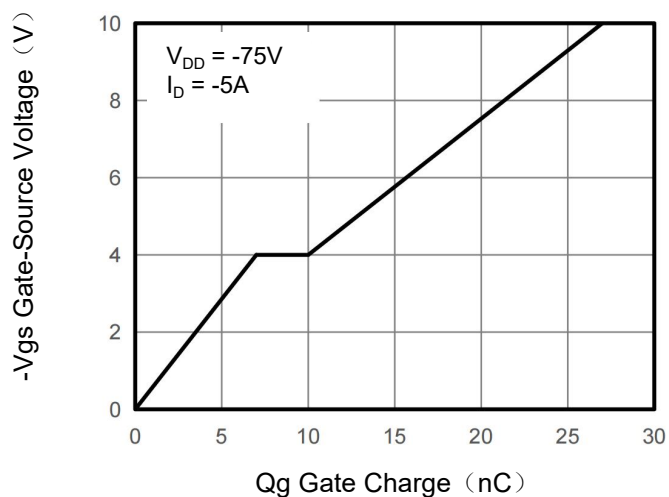


Figure 5. Capacitance

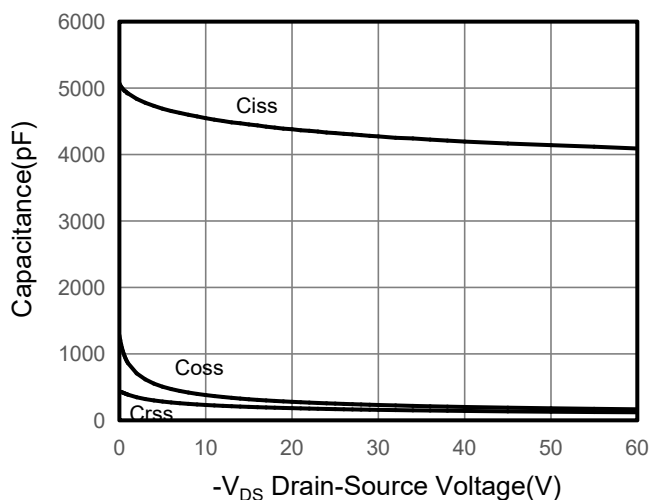
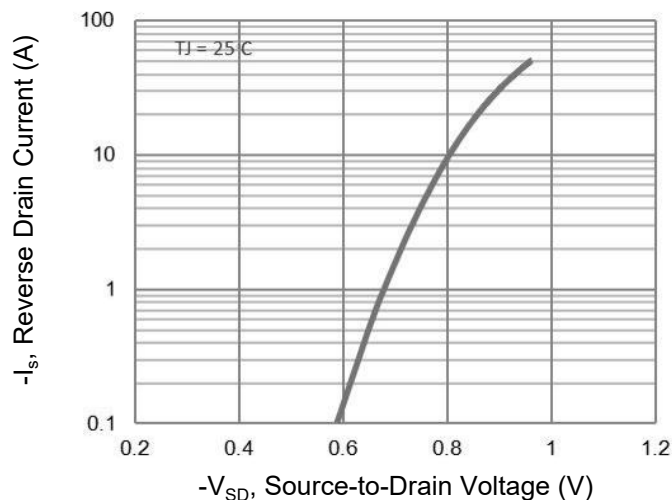


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

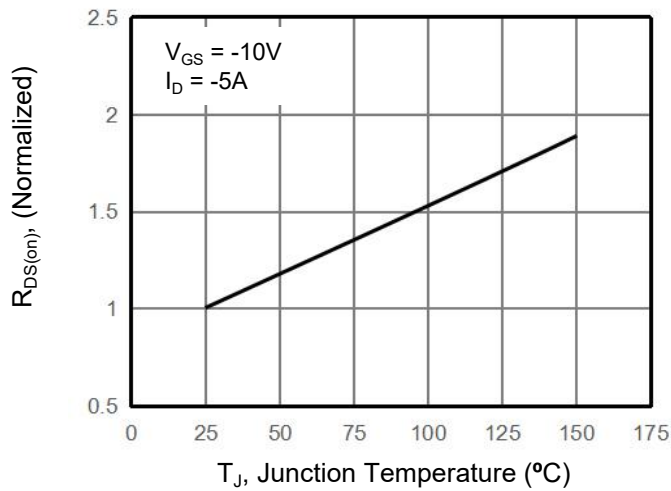


Figure 10. Safe Operation Area

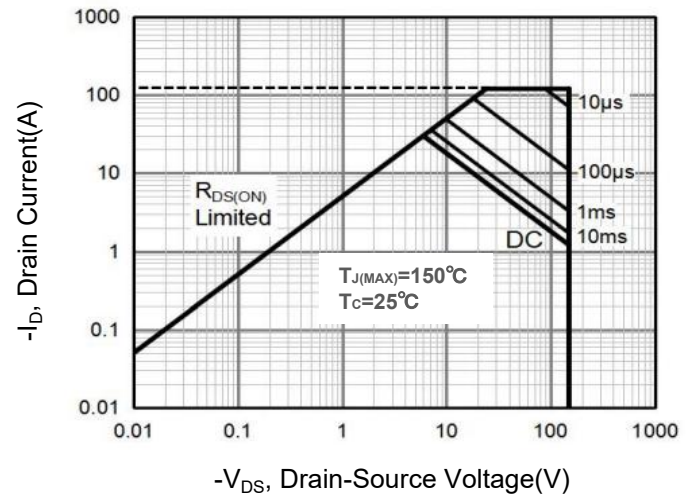
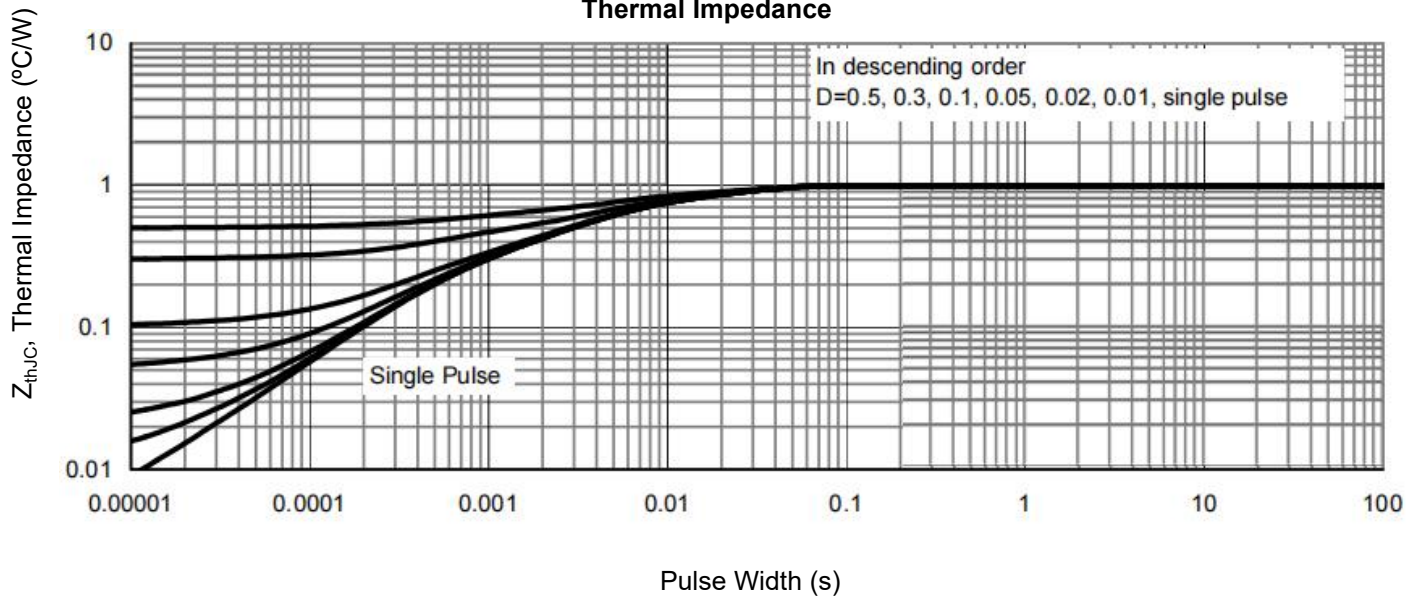
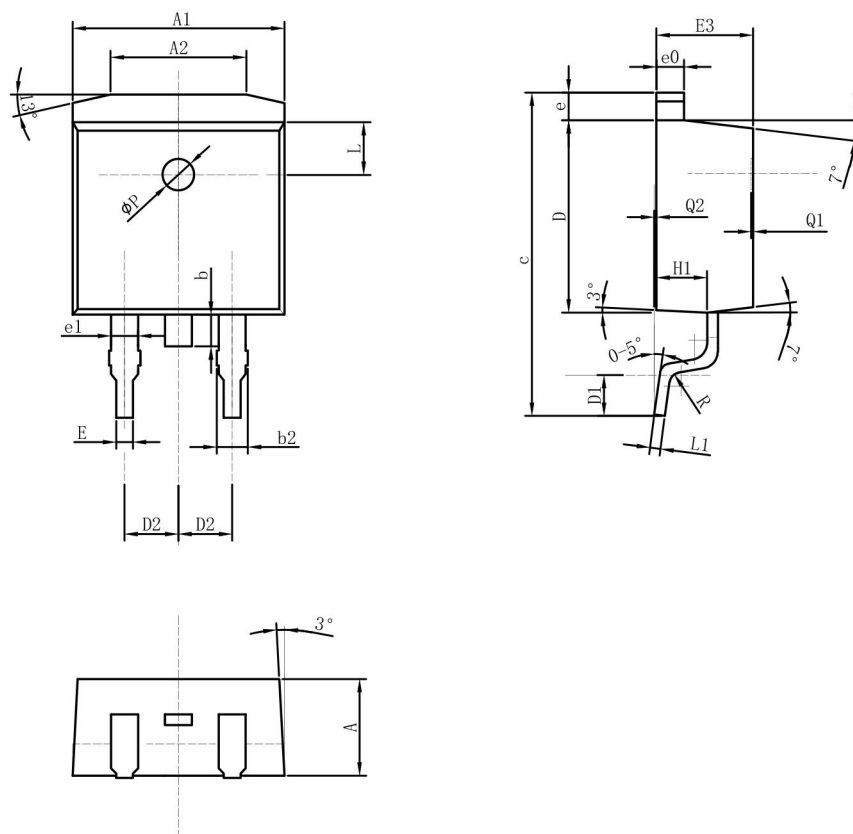


Figure 9. Normalized Maximum Transient Thermal Impedance



TO-263 Package Information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	4.52	4.57	4.62
A1	9.95	10.00	10.05
A2	6.30	6.40	6.50
b	1.30	1.50	1.70
b2	1.17	1.27	1.37
c	14.80	15.00	15.20
D	9.05	9.10	9.15
D1	1.90	2.10	2.30
D2	—	2.54	—
E	—	0.80	—
E3	—	4.57	—
e	—	1.30	—
e0	—	1.30	—
e1	1.73	3	—
H1	—	2.40	—
L	—	2.50	—
L1	—	0.50	—
ϕP	—	1.50	—
R	—	0.50	—
Q1	0.10	—	0.15
Q2	0	—	0.02